

## Description

Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N2219J)
- JANTX level (2N2219JX)
- JANTXV level (2N2219JV)
- JANS level (2N2219JS)
- JANSR level (2N2219JSR)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV and JANS
- Radiation testing (total dose) upon request

Please contact SEMICOA for special configurations  
[www.SEMICOA.com](http://www.SEMICOA.com) or (714) 979-1900

## Applications

- General purpose
- Low power
- NPN silicon transistor



## Features

- Hermetically sealed TO-39 metal can
- Also available in chip configuration
- Chip geometry 0400
- Reference document:  
MIL-PRF-19500/251

## Benefits

- Qualification Levels: JAN, JANTX, JANTXV, JANS and JANSR
- Radiation testing available

Absolute Maximum Ratings		$T_C = 25^\circ\text{C}$ unless otherwise specified	
Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	30	Volts
Collector-Base Voltage	$V_{CBO}$	60	Volts
Emitter-Base Voltage	$V_{EBO}$	5	Volts
Collector Current, Continuous	$I_C$	800	mA
Power Dissipation, $T_A = 25^\circ\text{C}$ Derate linearly above $25^\circ\text{C}$	$P_T$	0.8 4.6	W mW/ $^\circ\text{C}$
Power Dissipation, $T_C = 25^\circ\text{C}$ Derate linearly above $25^\circ\text{C}$	$P_T$	3.0 17.0	W mW/ $^\circ\text{C}$
Operating Junction Temperature	$T_J$	-55 to +200	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 to +200	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS

characteristics specified at  $T_A = 25^\circ\text{C}$

### Off Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}$	30			Volts
Collector-Base Cutoff Current	$I_{CBO1}$	$V_{CB} = 60\text{ Volts}$			10	$\mu\text{A}$
Collector-Base Cutoff Current	$I_{CBO2}$	$V_{CB} = 50\text{ Volts}$			10	nA
Collector-Base Cutoff Current	$I_{CBO3}$	$V_{CB} = 50\text{ Volts}, T_A = 150^\circ\text{C}$			10	$\mu\text{A}$
Collector-Emitter Cutoff Current	$I_{CES}$	$V_{CE} = 30\text{ Volts}$			10	nA
Emitter-Base Cutoff Current	$I_{EBO1}$	$V_{EB} = 5\text{ Volts}$			10	$\mu\text{A}$
Emitter-Base Cutoff Current	$I_{EBO2}$	$V_{EB} = 4\text{ Volts}$			10	nA

### On Characteristics

Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	$h_{FE1}$	$I_C = 0.1\text{ mA}, V_{CE} = 10\text{ Volts}$	35			
	$h_{FE2}$	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ Volts}$	50			
	$h_{FE3}$	$I_C = 10\text{ mA}, V_{CE} = 10\text{ Volts}$	75		325	
	$h_{FE4}$	$I_C = 150\text{ mA}, V_{CE} = 10\text{ Volts}$	100			
	$h_{FE5}$	$I_C = 500\text{ mA}, V_{CE} = 10\text{ Volts}$	30		300	
	$h_{FE6}$	$I_C = 10\text{ mA}, V_{CE} = 10\text{ Volts}$ $T_A = -55^\circ\text{C}$	15			
Base-Emitter Saturation Voltage	$V_{BEsat1}$	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$	0.6		1.3	Volts
	$V_{BEsat2}$	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			2.6	
Collector-Emitter Saturation Voltage	$V_{CEsat1}$	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$			0.4	Volts
	$V_{CEsat2}$	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			1.6	

### Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{FE} $	$V_{CE} = 20\text{ Volts}, I_C = 20\text{ mA}, f = 100\text{ MHz}$	2.5		12	
Small Signal Short Circuit Forward Current Transfer Ratio	$h_{FE}$	$V_{CE} = 10\text{ Volts}, I_C = 1\text{ mA}, f = 1\text{ kHz}$	50			
Open Circuit Output Capacitance	$C_{OBO}$	$V_{CB} = 10\text{ Volts}, I_E = 0\text{ mA}, 100\text{ kHz} < f < 1\text{ MHz}$			8	pF
Open Circuit Input Capacitance	$C_{IBO}$	$V_{EB} = 0.5\text{ Volts}, I_C = 0\text{ mA}, 100\text{ kHz} < f < 1\text{ MHz}$			25	pF

### Switching Characteristics

Saturated Turn-On Time	$t_{ON}$				40	ns
Saturated Turn-Off Time	$t_{OFF}$				250	ns